

Please amend the abstract at page 81, lines 1-10, as follows:

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device includes a first wiring extending in a first direction, a second wiring extending in a second direction differing from the first direction, and a magneto resistive element arranged between the first and second wirings and ~~comprising~~ including a first portion and a second portion, the second portion being in contact with the second wiring and extending along the second wiring to reach an outside region positioned outside the first portion.